

1.	Title of the course	Physics and Modeling of Semiconductor Devices
2.	Course number	EE542L
3.	Structure of credits	3-1-0-4
4.	Offered to	PG
5.	New course/modification to	Modification To EE5039/16
6.	To be offered by	Department of Electrical Engineering
7.	To take effect from	July 2022
8.	Prerequisite	Nil
9.	Course Objective(s): To provide in-depth understanding of semiconductor device physics and operation.	
10.	Course Content: Semiconductors: energy bands, thermal equilibrium carrier concentration, excess carriers, quasi Fermi levels, recombination of carriers, carrier lifetime; Carrier transport: drift, mobility, diffusion, continuity equation, diffusion length; Quantitative theory of PN junctions: equilibrium analysis, steady state I-V characteristics under forward bias, reverse bias and illumination, capacitances, dynamic behavior under small and large signals, breakdown mechanisms; Bipolar junction transistors: physics and characteristics; Hetero junctions and HBT; Metal-semiconductor junctions: Schottky diode, Ohmic contact; Theory of Field Effect Transistors: analysis of MOS capacitor, calculation of threshold voltage, static I-V characteristics of MOSFETs and their models; Other devices: LEDs, solar cells.	
11.	Textbook(s): 1. Streetman B G and Banerjee S K, <i>Solid State Electronic Devices</i> , 5th Edition, Prentice Hall India (2000). 2. Tyagi M S, <i>Introduction to Semiconductor Materials and Devices</i> , 1st Edition, Wiley (2008).	
12.	Reference(s): 1. Pierret R F, <i>Advanced Semiconductor Fundamentals, Vol. VI in the Modular Series on Solid State Devices</i> , 2nd Edition, Pearson Education (2003). 2. Sah C T, <i>Fundamentals of Solid State Electronics</i> , 1st Edition, World Scientific (1991). 3. Sze S M and Kwok K Ng, <i>Physics of Semiconductor Devices</i> , 3rd Edition, Wiley (2006). 4. Taur Y and Ning T H, <i>Fundamentals of Modern VLSI Devices</i> , 2nd Edition, Cambridge University Press (2009).	